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INFORMATION DISCLOSURE STATEMENT**

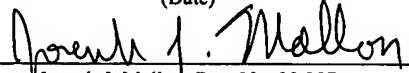
Applicant : Michael A. Todd
App. No : 10/783,044
Filed : February 19, 2004
For : PROCESS FOR DEPOSITING LOW
DIELECTRIC CONSTANT MATERIALS
Examiner : Archene A. Turner
Art Unit : 1775

CERTIFICATE OF MAILING

I hereby certify that this correspondence and all marked attachments are being deposited with the United States Postal Service as first-class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on

June 22, 2005

(Date)

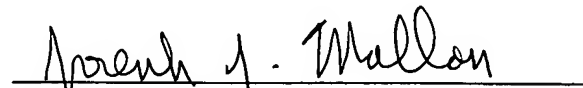

Joseph J. Mallon, Reg. No. 39,287

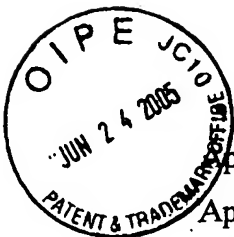
Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Enclosed for filing in the above-identified application are:

- (X) A courtesy copy of the Information Disclosure Statement and PTO/SB/08 equivalent filed on February 19, 2004 listing references for consideration:
 - (X) Listing seventy three (73) references.
 - (X) Enclosing 40 references.
- (X) The Commissioner is hereby authorized to charge any additional fees which may be required, or credit any overpayment, to Account No. 11-1410.
- (X) Return prepaid postcard.


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INFORMATION DISCLOSURE STATEMENT

Applicant : Michael A. Todd
App. No. : Filed herewith
Filed : Filed herewith
For : PROCESS FOR DEPOSITING LOW
DIELECTRIC CONSTANT MATERIALS
Examiner : Unknown
Group Art Unit : Unknown

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Enclosed is form PTO-1449 listing seventy-three (73) references that are of record in U.S. patent application No. 09/779,397, filed February 7, 2001, which is the parent of this divisional application, and is relied upon for an earlier filing date under 35 U.S.C. § 120. Copies of the references are not submitted pursuant to 37 C.F.R. § 1.98(d).

This Information Disclosure Statement is being filed with an RCE or within three months of the filing date of this application and no fee is required in accordance with 37 C.F.R. § 1.97(b)(1), (b)(2), or (b)(4).

Respectfully submitted,
KNOBBE, MARTENS, OLSON & BEAR, LLP

Dated: 2/19/2004

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FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
ASMJP.065DV1APPLICATION NO.
Filed herewithINFORMATION DISCLOSURE STATEMENT
BY APPLICANTAPPLICANT
Michael A. ToddFILING DATE
Filed HerewithGROUP
Unknown

(USE SEVERAL SHEETS IF NECESSARY)

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
	1.	4,781,942	11/01/88	Leyden et al.			
	2.	4,863,755	09/05/89	Hess et al.			
	3.	4,894,352	01/16/90	Lane et al.			
	4.	4,992,306	02/12/91	Hochberg et al.			
	5.	5,011,706	04/30/91	Tarhay et al.			
	6.	5,028,566	07/02/91	Legendijk			
	7.	5,231,058	07/27/93	Maeda et al.			
	8.	5,240,813	08/31/93	Watanabe et al.			
	9.	5,244,698	09/14/93	Ishihara et al.			
	10.	5,314,724	05/24/94	Tsukune et al.			
	11.	5,324,539	06/28/94	Maeda et al.			
	12.	5,380,555	01/10/95	Mine et al.			
	13.	5,433,786	07/18/95	Hu et al.			
	14.	5,494,712	02/27/96	Hu et al.			
	15.	5,554,570	09/10/96	Maeda et al.			
	16.	5,563,105	10/08/96	Dobuzinsky et al.			
	17.	5,703,404	12/30/97	Matsuura			
	18.	5,840,821	11/24/98	Nakano et al.			
	19.	5,876,798	03/02/99	Vassiliev			
	20.	5,989,998	11/23/99	Sugahara et al.			
	21.	5,998,522	12/07/99	Nakano et al.			
	22.	6,004,730	12/21/99	Mikoshiba et al.			
	23.	6,045,877	04/04/00	Gleason et al.			
	24.	6,051,321	04/18/00	Lee et al.			
	25.	6,051,508	04/18/00	Takase et al.			
	26.	6,054,379	04/25/00	Yau et al.			
	27.	6,068,884	05/30/00	Rose et al.			

EXAMINER

DATE CONSIDERED

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FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)	ATTY. DOCKET NO. ASMJP.065DV1	APPLICATION NO. Filed herewith
	APPLICANT Michael A. Todd	
	FILING DATE Filed Herewith	GROUP Unknown

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
	28.	6,245,690	06/12/01	Yau et al.			
	29.	6,258,407	07/10/01	Lee et al.			
	30.	6,303,047	10/16/01	Aronowitz et al.			
	31.	6,340,628	01/22/02	Van Cleemput et al.			
	32.	6,432,846	08/13/02	Matsuki			
	33.	6,458,718	10/01/02	Todd			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	34.	EP 0 436 185 B1	03/20/96	EPO				
	35.	EP 0 706 216 A2	04/10/96	Europe				
	36.	EP 0 723 600 B1	07/07/99	EPO				
	37.	EP 0 771 886 A1	05/07/97	EPO				
	38.	EP 0 960 958 A2	12/01/99	EPO				
	39.	EP 0 935 283 A2	08/11/99	EPO				
	40.	EPO 367 004 B1	12/15/93	EPO				
	41.	JP 09 293716A	11/11/97	Japan				
	42.	JP 11 176829 A	07/02/99	Japan				
	43.	WO 97/40207	10/30/97	PCT				
	44.	WO 97/41592	11/06/97	PCT				
	45.	WO 99/21706	05/06/99	PCT				
	46.	WO 99/41423	08/19/99	PCT				
	47.	WO 99/55526	11/04/99	PCT				
	48.	WO 99/60621	11/25/99	PCT				

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		FILING DATE Filed Herewith	GROUP Unknown

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
	49. Bayer et al., <i>Overall kinetics of SiO_x remote-PECVD using different organosilicon monomers</i> , Surface and Coatings Technology, 116-119 (1999) 874-878
	50. Berjoan et al., <i>XPS and XPS valence band characterizations of amorphous or polymeric silicon based thin films prepared by PACVD from organosilicon monomers</i> , J. Phys. IV France 9 (1999) pp. 1059-1068.
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	52. Chandrasekhar et al., "New Silicon-Carbon Materials Incorporating Si ₄ C Building Blocks," Mat. Res. Soc. Symp. Proc., Vol., 441, Materials Research Society, (1997)
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	55. Fonseca et al., <i>Plasma Polymerization of Tetramethylsilane</i> , Am. Chemical Society, 1993, 5, 1676-1682
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	57. Indrajit Banerjee, et al., "Characterization of Chemical Vapor Deposited Amorphous Fluorocarbons for Low Dielectric Constant Interlayer Dielectrics." J. Electrochem. Soc., Vol. 146(6), p. 2219 (1999).
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	FILING DATE Filed Herewith	GROUP Unknown

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
	70.	Sugahara et al., <i>Low Dielectric constant carbon containing SiO2 films deposited by PECVD technique using a novel CVD precursor</i> , DUMIC Conference, Feb. 10-11, 1997, pp. 19-25
	71.	Thomas et al., <i>Plasma etching and surface analysis of a SiC:H films deposited by low temperature plasma enhanced chemical vapor deposition</i> , Mat. Res. Soc. Symp. Proc. Vo. 334, 1994, pp. 445-450
	72.	Varma, Ravi, "Organosilylation: Synthesis and Characterization of Silylmethyl Methyl Ether," INORG. NUCL. CHEM. LETTERS, Vol. 6, pp. 9-14, 1970.
	73.	Washburne, Stephen S., et al. "Chloraminosilanes: I: The Preparation of Chloro(Dimethylamino) Hydrogen Silanes," Inorg. Nucl. Chem. Letters Vol. 5, pp. 17-19, Pergamon Press.

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